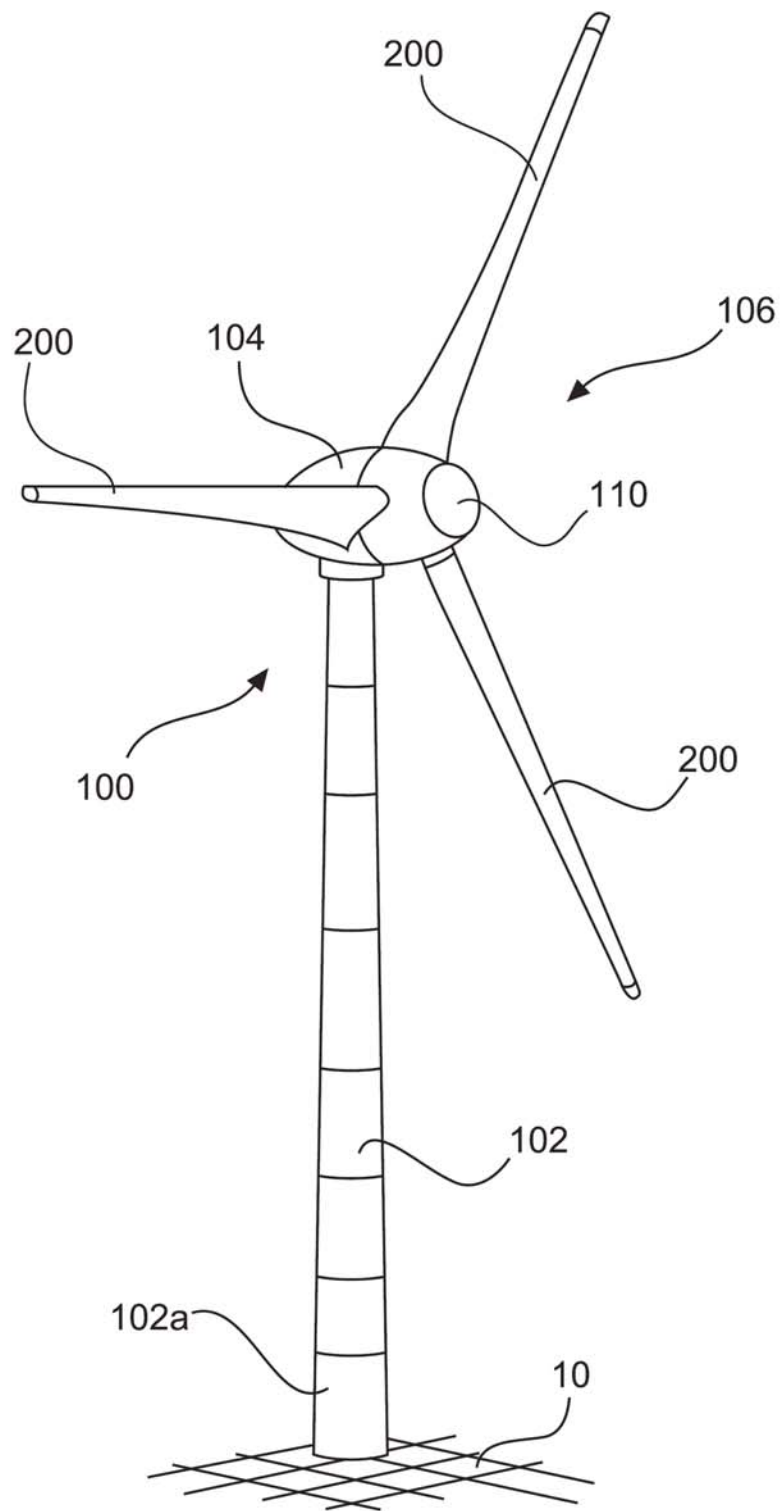
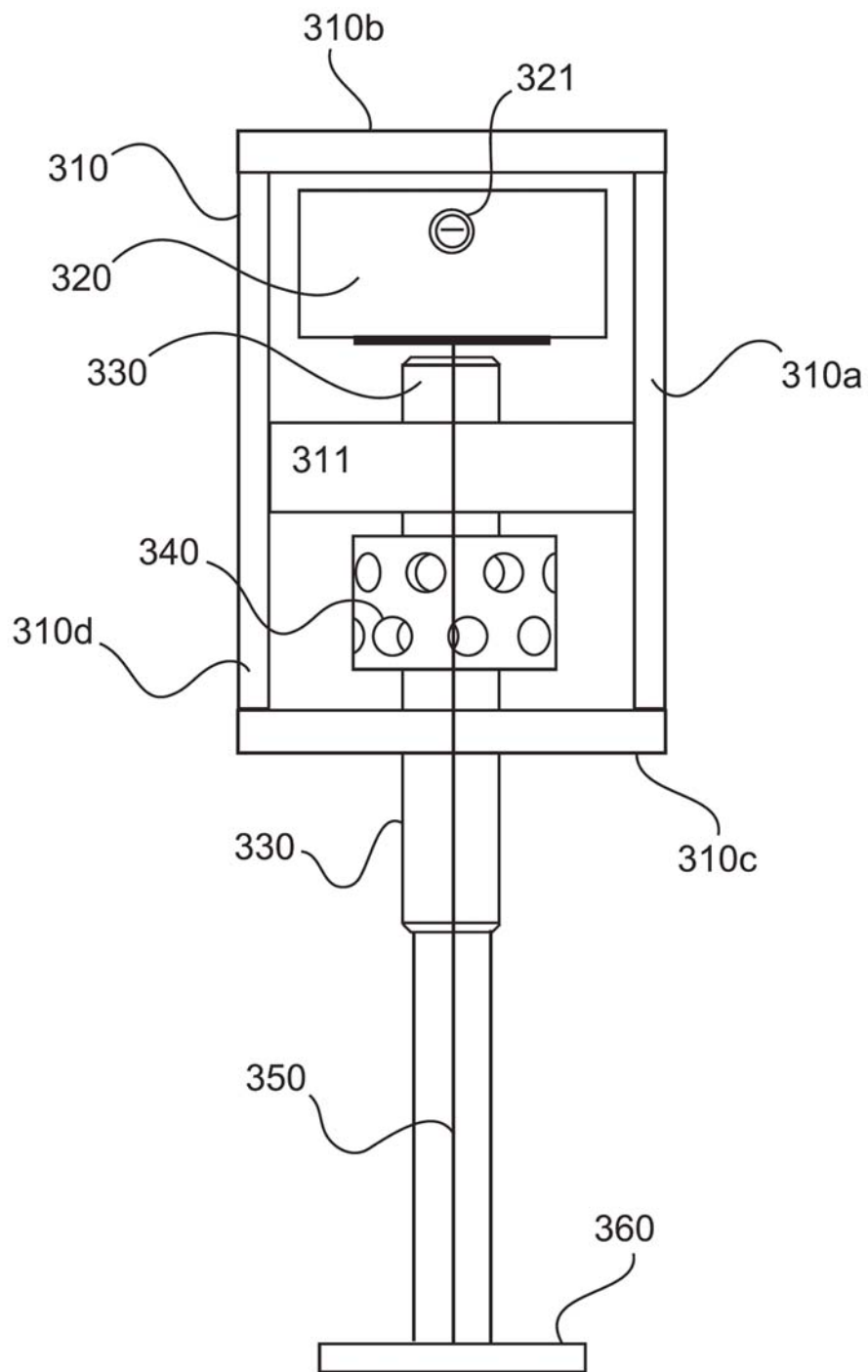
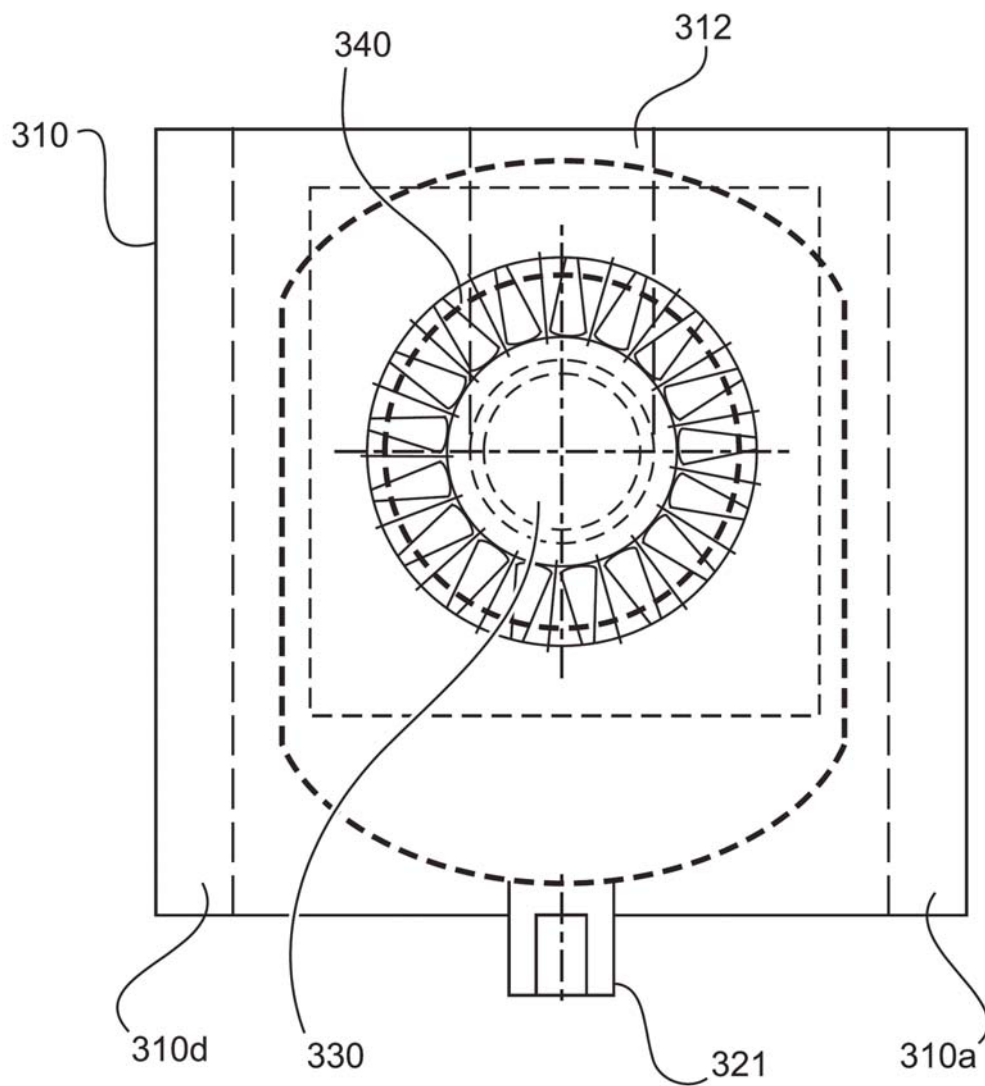


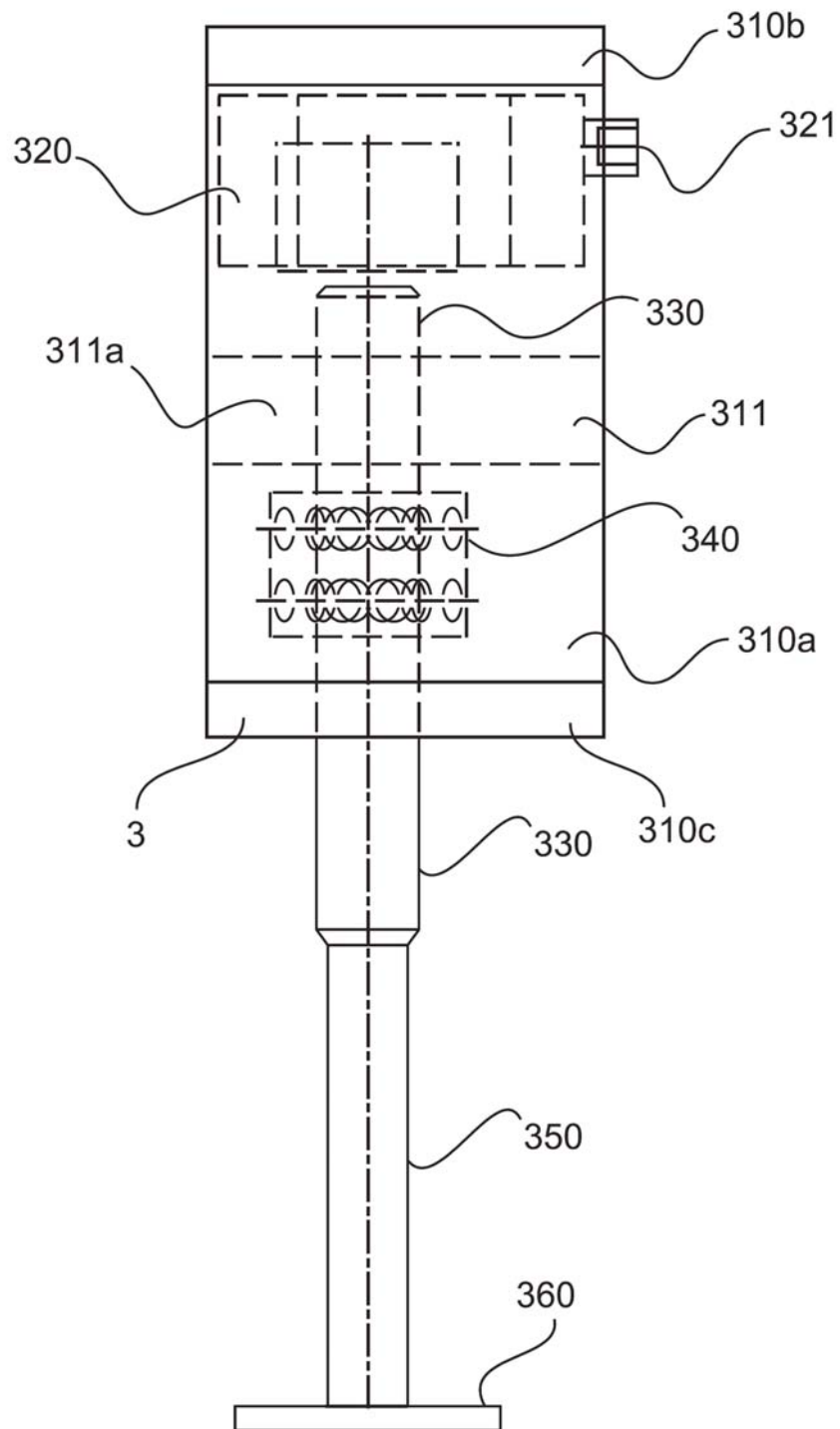
**Fig. 1**

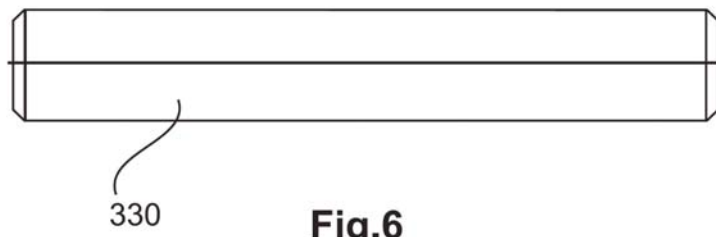
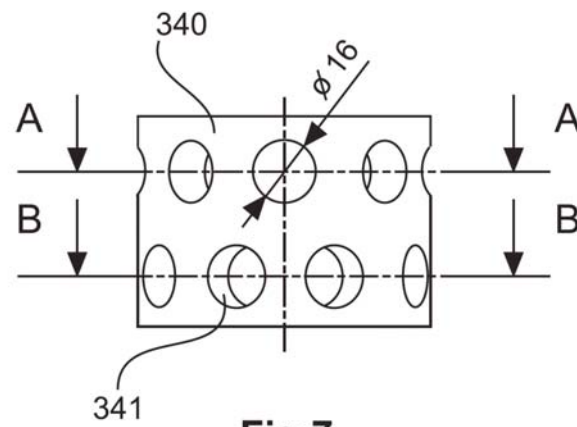
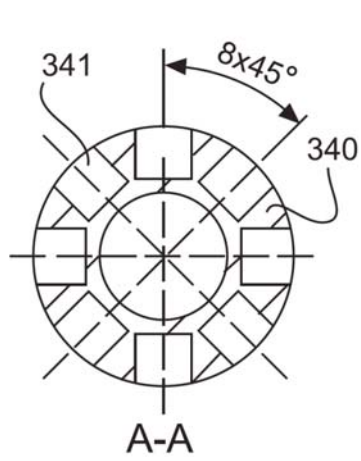
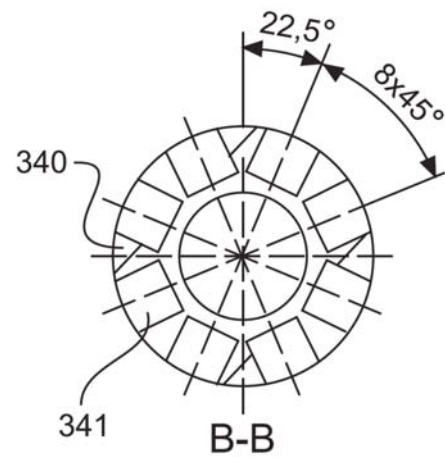
This cross-sectional view shows a substrate 10 with a trench 11. A layer 20 is formed on the bottom surface of the trench 11. A gate structure 350 is formed on the side walls of the trench 11. The gate structure 350 includes a gate oxide layer 360 and a gate electrode 370. The gate electrode 370 is formed on the side wall of the trench 11 and is electrically connected to a gate terminal 102a. The gate terminal 102a is formed on the top surface of the substrate 10. The gate oxide layer 360 is formed on the bottom surface of the trench 11 and is electrically connected to a gate terminal 102b. The gate terminal 102b is formed on the top surface of the substrate 10. The gate oxide layer 360 is also electrically connected to a gate terminal 102c. The gate terminal 102c is formed on the top surface of the substrate 10. The gate oxide layer 360 is also electrically connected to a gate terminal 102d. The gate terminal 102d is formed on the top surface of the substrate 10. The gate oxide layer 360 is also electrically connected to a gate terminal 102e. The gate terminal 102e is formed on the top surface of the substrate 10.

Fig. 2B

**Fig.3**

**Fig.4**

**Fig.5**

**Fig. 6****Fig. 7****Fig. 8A****Fig. 8B**